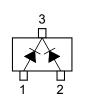
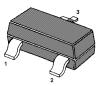
SILICON EPITAXIAL PLANAR SWITCHING DIODE

Application

• Ultra high speed switching





Marking Code: **A4** SOT-23 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	V _{RM}	80	V
Reverse Voltage	V _R	80	V
Average Forward Current	Ι _Ο	100	mA
Maximum Peak Forward Current	I _{FM}	300	mA
Surge Current (t = 1 µs)	I _{FSM}	4	А
Power Dissipation	P _{tot}	200	mW
Junction Temperature	Tj	150	°C
Storage Temperature Range	T _s	- 55 to + 150	°C

Characteristics at T_a = 25 °C

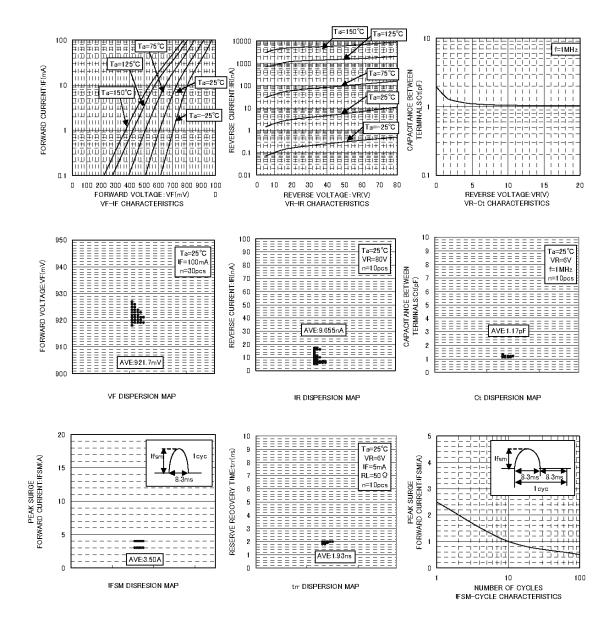
Parameter	Symbol	Max.	Unit
Forward Voltage at I _F = 100 mA	V _F	1.2	V
Reverse Current at V _R = 70 V	I _R	0.1	μA
Total Capacitance at V _R = 6 V, f = 1 MHz	C _T	3.5	pF
Reverse Recovery Time at V_R = 6 V, I_F = 5 mA, R_L = 50 Ω	t _{rr}	4	ns







Dated : 10/10/2008







Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



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